

PTO/SB/08A

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/038,084
Filing Date	January 3, 2002
Confirmation Number	7363
First Named Inventor	Robert J. Falster
Group Art Unit	2811
Examiner Name	
Attorney Docket No.	MEMC 98-3052 (2512.2)

Sheet 1 of 10

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
A.M.	1	4,314,595		Yamamoto et al.	02/16/1982
	2	4,376,657		Nagasawa et al.	03/15/1983
	3	4,437,922		Bishoff et al.	03/20/1984
	4	4,505,759		O'Mara	03/19/1985
	5	4,548,654		Tobin	10/22/1985
	6	4,851,358		Huber	07/25/1989
	7	4,868,133		Huber	09/19/1989
	8	4,981,549		Yamashita et al.	01/01/1991
	9	5,189,500		Kusunoki	02/23/1993
	10	5,264,189		Yamashita et al.	11/30/1993
	11	5,327,007		Imura et al.	07/05/1994
	12	5,401,669		Falster et al.	03/28/1995
	13	5,403,406		Falster et al.	04/04/1995
	14	5,436,175		Nakato et al.	07/25/1995

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
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Sheet	2	of	10	Attorney Docket No.	MEMC 98-3052 (2512.2)

P.M.	15	5,445,975		Gardner et al.	08/29/1995
	16	5,474,020		Bell et al.	12/12/1995
	17	5,478,408		Mitani et al.	12/26/1995
	18	5,485,803		Habu	01/23/1996
	19	5,487,354		von Ammon et al.	01/30/1996
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	33	5,788,763		Hayashi et al.	08/04/1998

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A.M	34	5,885,905		Nadahara et al.	03/23/1999
	35	5,939,770		Kageyama	08/17/1999
	36	5,944,889		Park et al.	08/31/1999
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	38	5,968,262		Saishouji et al.	10/19/1999
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	41	6,236,104		Falster	05/22/2001

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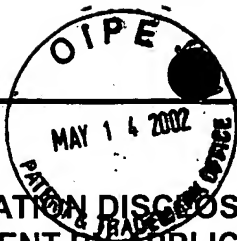
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
A.M	42	DE	3905626A1		Mitsubishi Kinzoku	08/31/1989	
	43	DE	4323964 A1		Tokyo Shibaura Electric Co.	01/20/1994	
	44	DE	4414947 A1		Wacker-Chemitronic	08/31/1995	
	45	DE	19806045 A1		Samsung Electronics	08/27/1998	
	46	EP	0504837 A2		Shin-Etsu Handota Co., Ltd	09/23/1992	
	47	EP	0503816 B1		Shin-Etsu Handota Co. Ltd	09/18/1992	
	48	EP	0536958 A1		Shin-Etsu Handotai Co. Ltd.	04/14/1993	

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A.M	49	EP	0716168 A1	Shin-Etsu Handotai Co. Ltd.	06/12/1996	
	50	EP	0799913	Leybold AG	12/08/1998	
	51	EP	0915502	Shin-Etsu Handotai K.K.	05/12/1999	
	52	EP	0954018	Sumitomo Metal Industries Ltd.	11/03/1999	
	53	EP	0962556 A1	Shin-Etsu Handotai Co. Ltd.	12/08/1999	
	54	GB	2182262	Sony Corporation	05/13/1986	
	55	JP	59119822 (Abstract)	Fujitsu Ltd.	07/11/1984	
	56	JP	2-32535	Kyushu Electronic Metal et al.	02/02/1988	X
	57	JP	1-242500	Mitsubishi Kinzoku Kabushiki Kaisha	09/27/1989	X
	58	JP	2180789 (Abstract only)	Kawasaki Steel Corp.	07/13/1990	
	59	JP	3-9078	Mitsubishi Metal K.K. Tokyo	02/07/1991	
	60	JP	3-185831	Komatsu Electronic Metals Co.	08/13/1991	X
	61	JP	4108682 (Abstract only)	Fuji Electric Co., Ltd.	04/09/1992	
	62	JP	4-294540	Nippon Steel Corp.	10/19/1992	X
	63	JP	5-155700 A	Nippon Steel Corp.	06/22/1993	
	64	JP	8-330316	Sumitomo Sitix Ltd.	05/31/1995	
	65	JP	7-201874 A	NEC Corp.	08/04/1995	

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A.M	66	JP	7321120 (Abstract only)		Komatsu Electron Metals Co. Ltd.	12/08/1995	
	67	JP	7335657 (Abstract only)		Komatsu Electron Metals Co. Ltd.	12/22/1995	
	68	JP	8045944 (Abstract only)		Sumitomo Sitix Corp.	02/16/1996	
	69	JP	8045947 (Abstract only)		Nippon Steel Corp.	02/16/1996	
	70	JP	8/045945		Mitsubishi Materials Corp.	02/16/1996	
	71	JP	8/268794		Sumitomo Sitix, Ltd.	10/15/1996	
	72	JP	8-293589 (Abstract)		Hitachi Ltd.	11/05/1996	
	73	JP	9/199416		Sumitomo Sitix Ltd.	07/31/1997	
	74	JP	9/202690		Shinetsu Semi-Conductor	08/05/1997	
	75	JP	9-326396 (Abstract)		Hitachi Ltd.	12/06/1997	
	76	JP	11-150119		Sunitomo Sitix Corp.	06/02/1999	
	77	JP	11-067781 A		Sunitomo Metal Ind. Ltd.	03/0/1999	
	78	JP	11-157995 A		Sunitomo Sitix Corp.	06/15/1999	
	79	JP	11-180800 A		Shin Etsu Handotai Co. Ltd.	07/06/1999	
	80	JP	11-189495 A		Sumitomo Metal Ind. Ltd.	07/13/1999	
	81	JP	11-199386 A		Shin Etsu Handotai Co. Ltd.	07/27/1999	

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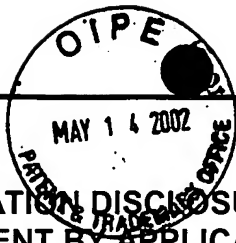
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A.M	82	JP	11-199387 A	Shin Etsu Handotai Co. Ltd.	07/27/1999
	83	WO	97/26393	Shin Etsu Handotai Co. Ltd.	07/24/1997
	84	WO	98/38675	MEMC Electronic Materials, Inc.	09/03/1998
	85	WO	98/45507	MEMC Electronic Materials, Inc.	10/15/1998
	86	WO	98/45508	MEMC Electronic Materials, Inc.	10/15/1998
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	88	WO	98/45510	MEMC Electronic Materials, Inc.	10/15/1998

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

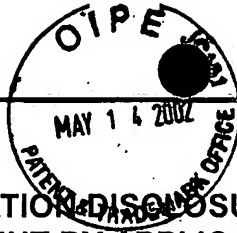
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
A.M	89	ABE, T., "Innovated Silicon Crystal Growth and Wafering Technologies" Electrochemical Society Proceedings, vol. 97, No. 3, pp. 123-133. (No Month).	
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	91	CHIOU, H.D., et al., "Gettering of Bonded Soi Layers", Proceedings of the International Symposium on Silicon-On-Insulator Technology and Devices, pp. 416-423	
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	93	de KOCK, A.J.R., et al., "The Effect of Doping on the Formation of Swirl Defects in Dislocation-Free Czochralski-Grown Silicon Crystals", Journal of Crystal Growth, Vol. 49, pp. 718-734, 1980.	

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				First Named Inventor	Robert J. Falster
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Sheet	7	of	10	Attorney Docket No.	MEMC 98-3051 (2512.1)

A.M	94	DORNBERGER, E., et al., "The Dependence Ring Like Distributed Stacking Faults on the Axial Temperature Gradient of Growing Czochralski Silicon Crystals", Electrochemical Society Proceedings, vol. 95-4, (May 1995) pp. 294-305	
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	98	EIDENZON, A.M., et al., "Defect-free Silicon Crystals Grown by The Czochralski Technique", Inorganic Materials, Vol. 33, No. 3 (1977) pp.219-225	
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A.M	105	HOURAI, M., et al. "Growth Parameters Determining the Type of Grown-In Defects in Czochralski Silicon Crystals", Materials Science Forum, Vols. 196-201 (1995) pp. 1713-1718	
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Attorney Docket No.

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Examiner
Signature

ANH D. MAI

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	09/737,715
Filing Date	December 15, 2000
Confirmation Number	9249
First Named Inventor	Robert J. Falster
Group Art Unit	
Examiner Name	
Attorney Docket No.	MEMC 98-3051 (2512.1)

Sheet 10 of 10

A.M	129	VORONKOV, V., et al., "Grown-in microdefects, residual vacancies and oxygen precipitation banks in Czochralski silicon" Journal of Crystal Growth, 304 (1999) pp. 462-474	
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Examiner Signature	ANH D. MAI	Date Considered	5/02/03
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